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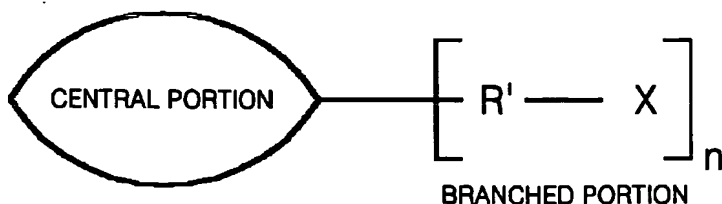
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ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: LOW DIELECTRIC ORGANOSILICATE POLYMER COMPOSITE



(57) Abstract: Provided are a porous organosilicate polymer composite prepared by heating an organic/inorganic hybrid polymer in which an organosilicate polymer is chemically bonded to a radial pore-forming polymer ended with a hydrolyzable alkoxy-silyl group and used as a core molecule, and a semiconductor device using an organosilicate polymer composite film including the porous organosilicate polymer composite. The organosilicate polymer

composite film has a very low dielectric constant, and thus, is useful as a dielectric film of the semiconductor device.

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